

**FORM PTO-1449 U.S. Department of Commerce**  
**Patent and Trademark Office**
**Attorney Docket Number**  
 5308-168

**Serial No.**  
 09/878,442

**LIST OF DOCUMENTS CITED BY APPLICANT**

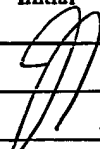
(Use several sheets if necessary)

**Applicants:** Das et al.

**Filing Date:** June 11, 2001

**Group**  
 2815

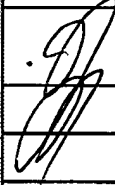
**U. S. PATENT DOCUMENTS**

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1	5,587,870	12/24/96	Anderson et al.	361	313

**FOREIGN PATENT DOCUMENTS**

Document Number	Date	Country	Class	Subclass	Translation Yes   No

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

	2	Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric," <i>IEEE Transactions on Electron Devices</i> . Vol. 47, No. 2, February 2000. ✓
	3	Invitation to Pay Additional Fees for PCT/US02/09393 dated 7/7/03. ✓

**EXAMINER**  
**\*EXAMINER**
**DATE CONSIDERED**

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

11/03